

**FEATURES**

- Ideal for Electron Detection
- Large Detection Area
- Protective Cover Plate<sup>3</sup>

**Electro-Optical Characteristics at 25 °C**

Parameters	Test Conditions	Min	Typ	Max	Units
Active Area	100 mm x 100 mm		100		mm <sup>2</sup>
Responsivity	@ 254 nm, V <sub>R</sub> = 0 V	0.07	0.08	0.09	A/W
Shunt Resistance, R <sub>sh</sub>	V <sub>B</sub> = ± 10 mV	20			M-ohm
Reverse Breakdown Voltage, V <sub>R</sub>	I <sub>R</sub> = 1 μA	5	10		Volts
Capacitance, C	V <sub>R</sub> = 0 V		5	15	nF
Rise Time	V <sub>R</sub> = 0 V, R <sub>L</sub> = 50 Ω			10	usec

**Thermal Parameters**

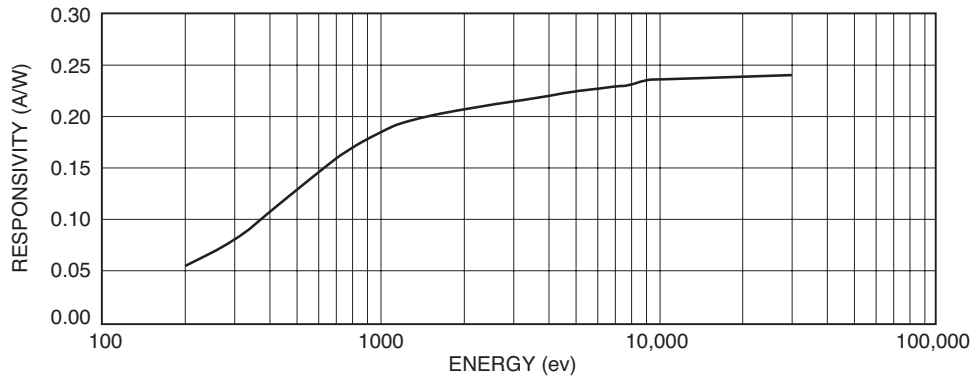
Storage and Operating Temperature Range	Units
Ambient <sup>1</sup>	-10 ° to 40 °C
Nitrogen or Vacuum	-20 °C to 80 °C
Lead Soldering Temperature <sup>2</sup>	260 °C

<sup>1</sup> Temperatures exceeding these parameters may create oxide growth on the active area. Over time responsivity to low energy radiation and wavelengths below 150 nm will be compromised.

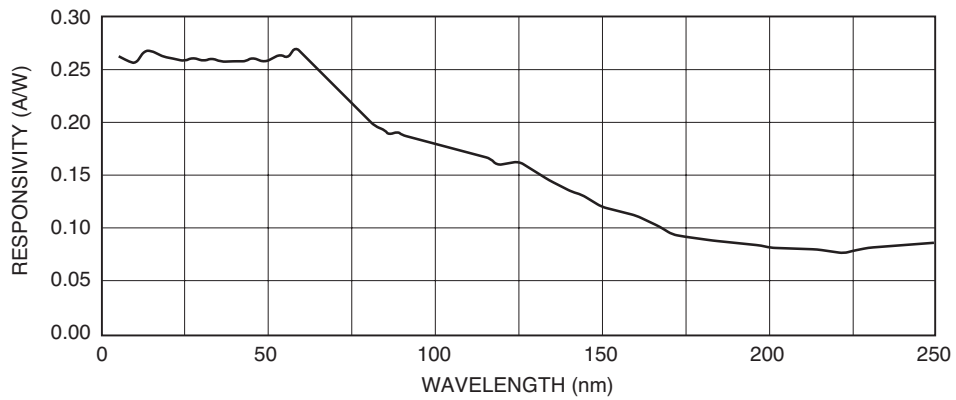
<sup>2</sup> 0.080" from case for 10 seconds.

<sup>3</sup> Shipped with temporary cover to protect the photodiode array and wire bonds. Review the Application Note, "Handling Precautions for AXUV, SXUV, and UVG Detectors", prior to removing cover.

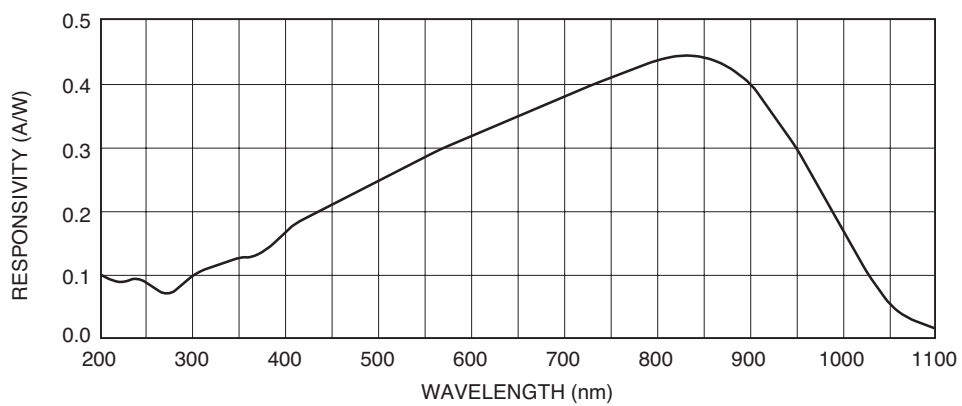
**Typical Electron Response**



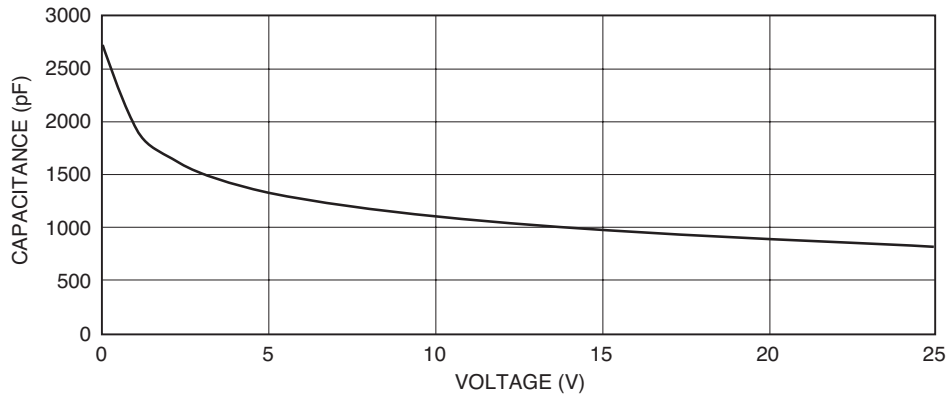
**Typical EUV-UV Photon Response**



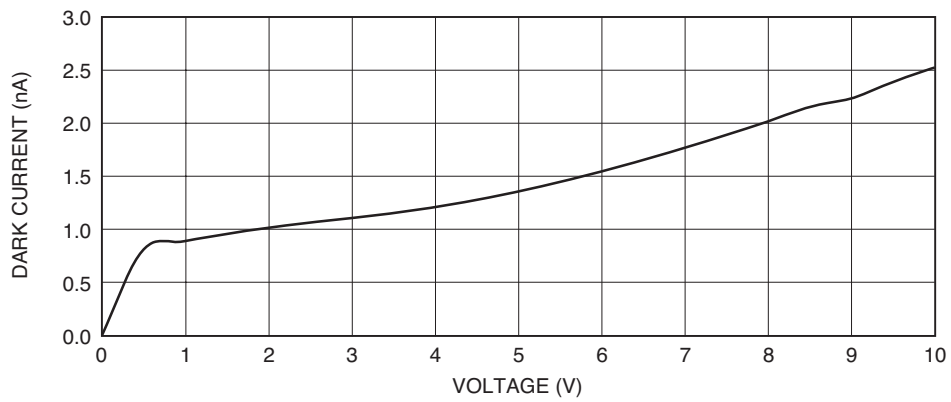
**Typical UV-VIS-NIR Photon Responsivity**



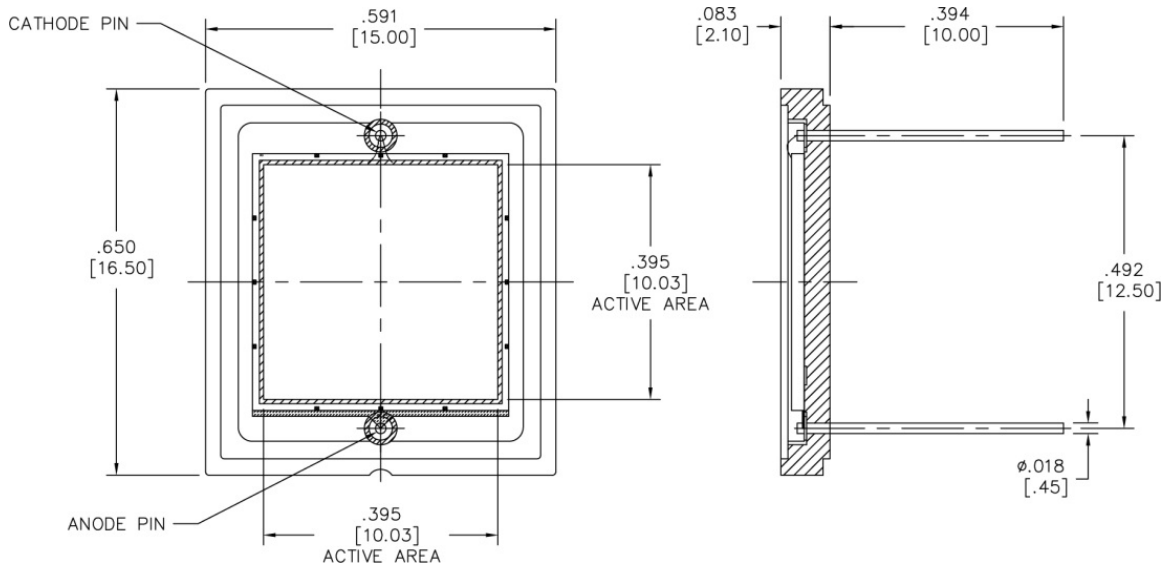
**Capacitance vs. Voltage**



**Dark Current vs. Voltage**



**Package Information**



Dimensions are in inch [metric] units.

Specifications are subject to change without prior notice.